TPD4E02B04 4-Channel ESD Protection Diode for USB Type-C and HDMI 2.0

1 Features
- IEC 61000-4-2 Level 4 ESD Protection
  - ±12-kV Contact Discharge
  - ±15-kV Air Gap Discharge
- IEC 61000-4-4 EFT Protection
  - 80 A (5/50 ns)
- IEC 61000-4-5 Surge Protection
  - 2 A (8/20 µs)
- IO Capacitance:
  - 0.25 pF (Typical)
  - 0.33 pF (Maximum)
- DC Breakdown Voltage: 5.5 V (Minimum)
- Ultra Low Leakage Current: 10 nA (Maximum)
- Low ESD Clamping Voltage: 8.8 V at 5-A TLP
- Supports High Speed Interfaces up to 10 Gbps
- Industrial Temperature Range: −40°C to +125°C
- Easy Flow-Through Routing Package

2 Applications
- End Equipment
  - Laptops and Desktops
  - Set-Top Boxes
  - TV and Monitors
  - Mobile and Tablets
  - DVR and NVR

3 Description
The TPD4E02B04 is a bidirectional TVS ESD protection diode array for USB Type-C and HDMI 2.0 circuit protection. The TPD4E02B04 is rated to dissipate ESD strikes at the maximum level specified in the IEC 61000-4-2 international standard (Level 4).

This device features a 0.25-pF IO capacitance per channel making it ideal for protecting high-speed interfaces up to 10 Gbps such as USB 3.1 Gen2. The low dynamic resistance and low clamping voltage ensure system level protection against transient events.

The TPD4E02B04 is offered in the industry standard USON-10 (DQA) package. The package features flow-through routing and 0.5-mm pin pitch easing implementation and reducing design time.

Device Information

<table>
<thead>
<tr>
<th>PART NUMBER</th>
<th>PACKAGE</th>
<th>BODY SIZE (NOM)</th>
</tr>
</thead>
<tbody>
<tr>
<td>TPD4E02B04</td>
<td>USON (10)</td>
<td>2.50 mm × 1.00 mm</td>
</tr>
</tbody>
</table>

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Typical Application Schematic
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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (February 2016) to Revision B  Page

• Updated Capacitance spec in the Features, Description, IO Capacitance and Operating Frequency sections .... 1
• Made changes to Operating Frequency ................................................................. 1
• Updated Figure 15, Figure 16, Figure 22 and Figure 23 ........................................ 1

Changes from Original (November 2015) to Revision A  Page

• Changed device status from Product Preview to Production Data ........................................ 1
5 Pin Configuration and Functions

DQA Package 10-Pin USON Top View

<table>
<thead>
<tr>
<th>PIN</th>
<th>TYPE</th>
<th>DESCRIPTION</th>
</tr>
</thead>
<tbody>
<tr>
<td>GND</td>
<td>3</td>
<td>Ground. Connect to ground</td>
</tr>
<tr>
<td>GND</td>
<td>8</td>
<td>Ground. Connect to ground</td>
</tr>
<tr>
<td>IO1</td>
<td>1</td>
<td>I/O ESD protected channel</td>
</tr>
<tr>
<td>IO2</td>
<td>2</td>
<td>I/O ESD protected channel</td>
</tr>
<tr>
<td>IO3</td>
<td>4</td>
<td>I/O ESD protected channel</td>
</tr>
<tr>
<td>IO4</td>
<td>5</td>
<td>I/O ESD protected channel</td>
</tr>
<tr>
<td>NC</td>
<td>6</td>
<td>NC Not connected; Used for optional straight-through routing. Can be left floating or grounded</td>
</tr>
<tr>
<td>NC</td>
<td>7</td>
<td>NC Not connected; Used for optional straight-through routing. Can be left floating or grounded</td>
</tr>
<tr>
<td>NC</td>
<td>9</td>
<td>NC Not connected; Used for optional straight-through routing. Can be left floating or grounded</td>
</tr>
<tr>
<td>NC</td>
<td>10</td>
<td>NC Not connected; Used for optional straight-through routing. Can be left floating or grounded</td>
</tr>
</tbody>
</table>
6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

<table>
<thead>
<tr>
<th>MIN</th>
<th>MAX</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>Electrical fast transient</td>
<td>IEC 61000-4-5 (5/50 ns)</td>
<td>80 A</td>
</tr>
<tr>
<td>Peak pulse</td>
<td>IEC 61000-4-5 Power (t_p - 8/20 µs)</td>
<td>17 W</td>
</tr>
<tr>
<td></td>
<td>IEC 61000-4-5 Current (t_p - 8/20 µs)</td>
<td>2 A</td>
</tr>
<tr>
<td>T_A</td>
<td>Operating free-air temperature</td>
<td>–40 125 °C</td>
</tr>
<tr>
<td>T_stg</td>
<td>Storage temperature</td>
<td>–65 155 °C</td>
</tr>
</tbody>
</table>

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

<table>
<thead>
<tr>
<th>VALUE</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>V_(ESD)</td>
<td>Electrostatic discharge</td>
</tr>
<tr>
<td>±2500</td>
<td>V</td>
</tr>
<tr>
<td>±1000</td>
<td>V</td>
</tr>
</tbody>
</table>

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 ESD Ratings—IEC Specification

<table>
<thead>
<tr>
<th>VALUE</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>V_(ESD)</td>
<td>Electrostatic discharge</td>
</tr>
<tr>
<td>±12000</td>
<td>V</td>
</tr>
<tr>
<td>±15000</td>
<td>V</td>
</tr>
</tbody>
</table>

6.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

<table>
<thead>
<tr>
<th>MIN</th>
<th>MAX</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>V(IO)</td>
<td>Input pin voltage</td>
<td>–3.6 3.6 V</td>
</tr>
<tr>
<td>T_A</td>
<td>Operating free-air temperature</td>
<td>–40 125 °C</td>
</tr>
</tbody>
</table>

6.5 Thermal Information

<table>
<thead>
<tr>
<th>THERMAL METRIC(1)</th>
<th>TPD4E02B04 DQA (USON)</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>R_JJA</td>
<td>Junction-to-ambient thermal resistance</td>
<td>348.7</td>
</tr>
<tr>
<td>R_JJC(top)</td>
<td>Junction-to-case (top) thermal resistance</td>
<td>214.1</td>
</tr>
<tr>
<td>R_JJB</td>
<td>Junction-to-board thermal resistance</td>
<td>270.7</td>
</tr>
<tr>
<td>ψ_JT</td>
<td>Junction-to-top characterization parameter</td>
<td>81.7</td>
</tr>
<tr>
<td>ψ_JB</td>
<td>Junction-to-board characterization parameter</td>
<td>270.7</td>
</tr>
<tr>
<td>R_JJC(bot)</td>
<td>Junction-to-case (bottom) thermal resistance</td>
<td>N/A</td>
</tr>
</tbody>
</table>

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.
6.6 Electrical Characteristics
over operating free-air temperature range (unless otherwise noted)

<table>
<thead>
<tr>
<th>PARAMETER</th>
<th>TEST CONDITIONS</th>
<th>MIN</th>
<th>TYP</th>
<th>MAX</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>$V_{RW}$ Reverse stand-off voltage</td>
<td>$I_{IO} &lt; 10 \text{ nA}$</td>
<td>$-3.6$</td>
<td>$3.6$</td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>$V_{BR}$ Breakdown voltage, any IO pin to GND(1)</td>
<td>$I_{IO} = 1 \text{ mA, } T_{A} = 25^\circ C$</td>
<td>5.5</td>
<td>6.4</td>
<td>7.5</td>
<td>V</td>
</tr>
<tr>
<td>$V_{BB}$ Breakdown voltage, GND to any IO pin(1)</td>
<td>$I_{IO} = 1 \text{ mA, } T_{A} = 25^\circ C$</td>
<td>$-5.5$</td>
<td>$-6.4$</td>
<td>$-7.5$</td>
<td>V</td>
</tr>
<tr>
<td>$V_{HOL}$ Holding voltage(2)</td>
<td>$I_{IO} = 1 \text{ mA}$</td>
<td>5.8</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>$V_{CL}$ Clamping voltage</td>
<td>$I_{PP} = 1 \text{ A, TLP, from IO to GND}$</td>
<td>6.6</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td></td>
<td>$I_{PP} = 5 \text{ A, TLP, from IO to GND}$</td>
<td>8.8</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td></td>
<td>$I_{PP} = 1 \text{ A, TLP, from GND to IO}$</td>
<td>6.6</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td></td>
<td>$I_{PP} = 5 \text{ A, TLP, from GND to IO}$</td>
<td>8.8</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>$I_{LEA}$ Leakage current, any IO to GND</td>
<td>$V_{IO} = \pm 2.5 \text{ V}$</td>
<td></td>
<td></td>
<td>10</td>
<td>nA</td>
</tr>
<tr>
<td>$R_{DYN}$ Dynamic resistance</td>
<td>IO to GND</td>
<td>0.47</td>
<td></td>
<td></td>
<td>Ω</td>
</tr>
<tr>
<td></td>
<td>GND to IO</td>
<td>0.47</td>
<td></td>
<td></td>
<td>Ω</td>
</tr>
<tr>
<td>$C_{L}$ Line capacitance</td>
<td>$V_{IO} = 0 \text{ V, } f = 1 \text{ MHz, IO to GND, } T_{A} = 25^\circ C$</td>
<td>0.25</td>
<td>0.33</td>
<td></td>
<td>pF</td>
</tr>
<tr>
<td>$\Delta C_{L}$ Variation of line capacitance</td>
<td>Delta of capacitance between any two IO pins, $V_{IO} = 0 \text{ V, } f = 1 \text{ MHz, } T_{A} = 25^\circ C$, GND = 0 V</td>
<td>0.01</td>
<td>0.07</td>
<td></td>
<td>pF</td>
</tr>
<tr>
<td>$C_{CROSS}$ Channel to channel capacitance</td>
<td>Capacitance from one IO to another, $V_{IO} = 0 \text{ V, } f = 1 \text{ MHz, } GND = 0 \text{ V}$</td>
<td>0.13</td>
<td></td>
<td></td>
<td>pF</td>
</tr>
</tbody>
</table>

(1) $V_{BR}$ and $V_{BB}$ are defined as the voltage when 1 mA is applied in the positive-going direction, before the device latches into the snapback state.
(2) $V_{HOL}$ is defined as the voltage when 1 mA is applied in the negative-going direction, after the device has successfully latched into the snapback state.
6.7 Typical Characteristics

Figure 1. Positive TLP Curve

Figure 2. Negative TLP Curve

Figure 3. Surge Curve (t<sub>p</sub> = 8/20 µs), any IO pin to GND

Figure 4. 8-kV IEC Waveform

Figure 5. –8-kV IEC Waveform

Figure 6. Capacitance vs Bias Voltage
Typical Characteristics (continued)

Figure 7. Capacitance vs Ambient Temperature

Figure 8. Leakage Current vs Temperature

Figure 9. DC Voltage Sweep I-V Curve

Figure 10. Capacitance vs Frequency

Figure 11. 8-kV IEC Waveform through 2-m HDMI Cable

Figure 12. –8-kV IEC Waveform through 2-m HDMI Cable
Typical Characteristics (continued)

Figure 13. USB3.0 Eye Diagram (Bare Board)

Figure 14. USB3.0 Eye Diagram (With TPD4E02B04)

Figure 15. USB3.1 Gen 2 Eye Diagram (Bare Board)

Figure 16. USB3.1 Gen 2 Eye Diagram (With TPD4E02B04)

Figure 17. HDMI2.0 6-Gbps TP2 Eye Diagram (Bare Board)

Figure 18. HDMI2.0 6-Gbps TP2 Eye Diagram (With TPD4E02B04)
Typical Characteristics (continued)

Figure 19. Differential Insertion Loss
7 Detailed Description

7.1 Overview
The TPD4E02B04 is a bidirectional ESD Protection Diode with ultra-low capacitance. This device can dissipate ESD strikes above the maximum level specified by the IEC 61000-4-2 International Standard. The ultra-low capacitance makes this device ideal for protecting any super high-speed signal pins.

7.2 Functional Block Diagram

7.3 Feature Description

7.3.1 IEC 61000-4-2 ESD Protection
The I/O pins can withstand ESD events up to ±12-kV contact and ±15-kV air gap. An ESD-surge clamp diverts the current to ground.

7.3.2 IEC 61000-4-4 EFT Protection
The I/O pins can withstand an electrical fast transient burst of up to 80 A (5/50 ns waveform, 4 kV with 50-Ω impedance). An ESD-surge clamp diverts the current to ground.

7.3.3 IEC 61000-4-5 Surge Protection
The I/O pins can withstand surge events up to 2 A and 17 W (8/20 μs waveform). An ESD-surge clamp diverts the current to ground.

7.3.4 IO Capacitance
The capacitance between each I/O pin to ground is 0.25 pF (typical) and 0.33 pF (maximum). This device supports data rates up to 10 Gbps.

7.3.5 DC Breakdown Voltage
The DC breakdown voltage of each I/O pin is a minimum of ±5.5 V. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of ±3.6 V.

7.3.6 Ultra Low Leakage Current
The I/O pins feature an ultra-low leakage current of 10 nA (maximum) with a bias of ±2.5 V.

7.3.7 Low ESD Clamping Voltage
The I/O pins feature an ESD clamp that is capable of clamping the voltage to 8.8 V (I_{PP} = 5 A).

7.3.8 Supports High Speed Interfaces
This device is capable of supporting high speed interfaces up to 10 Gbps, because of the extremely low IO capacitance.
Feature Description (continued)

7.3.9 Industrial Temperature Range
This device features an industrial operating range of –40°C to +125°C.

7.3.10 Easy Flow-Through Routing Package
The layout of this device makes it simple and easy to add protection to an existing layout. The packages offers flow-through routing, requiring minimal modification to an existing layout.

7.4 Device Functional Modes
The TPD4E02B04 is a passive integrated circuit that triggers when voltages are above $V_{BRF}$ or below $V_{BRR}$. During ESD events, voltages as high as ±15 kV (air) can be directed to ground via the internal diode network. When the voltages on the protected line fall below the trigger levels of TPD4E02B04 (usually within 10s of nanoseconds) the device reverts to passive.
8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI’s customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TPD4E02B04 is a diode type TVS which is used to provide a path to ground for dissipating ESD events on high-speed signal lines between a human interface connector and a system. As the current from ESD passes through the TVS, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The low $R_{\text{DYN}}$ of the triggered TVS holds this voltage, $V_{\text{CLAMP}}$, to a safe level for the protected IC.

8.2 Typical Application

Figure 20. USB 3.1 Gen 2 Type-C ESD Schematic
Typical Application (continued)

Figure 21. USB 3.1 Gen 2 SuperSpeed Layout

8.2.1 Design Requirements

For this design example two TPD4E02B04 devices and two TPD4E05U06 devices are being used in a USB 3.1 Gen 2 Type-C application. This provides a complete ESD protection scheme.

Given the USB 3.1 Gen 2 Type-C application, the parameters listed in Table 1 are known.

<table>
<thead>
<tr>
<th>DESIGN PARAMETER</th>
<th>VALUE</th>
</tr>
</thead>
<tbody>
<tr>
<td>Signal Range on SuperSpeed+ Lines</td>
<td>0 V to 3.6 V</td>
</tr>
<tr>
<td>Operating Frequency on SuperSpeed+ Lines</td>
<td>5 GHz</td>
</tr>
<tr>
<td>Signal Range on CC, SBU, and DP/DM Lines</td>
<td>0 V to 5 V</td>
</tr>
<tr>
<td>Operating Frequency on CC, SBU, and DP/DM Lines</td>
<td>up to 480 MHz</td>
</tr>
</tbody>
</table>
8.2.2 Detailed Design Procedure

8.2.2.1 Signal Range

The TPD4E02B04 supports signal ranges between –3.6 V and 3.6 V, which supports the SuperSpeed+ pairs on the USB Type-C application. The TPD4E05U06 supports signal ranges between 0 V and 5.5 V, which supports the CC, SBU, and DP/DM lines.

8.2.2.2 Operating Frequency

The TPD4E02B04 has a 0.25 pF (typical) capacitance, which supports the USB3.1 Gen 2 data rates of 10 Gbps. The TPD4E05U06 has a 0.5 pF (typical) capacitance, which easily supports the CC, SBU, and DP/DM data rates.

8.2.3 Application Curves

![Figure 22. USB 3.1 Gen 2 10-Gbps Eye Diagram (Bare Board)](image1)

![Figure 23. USB 3.1 Gen 2 10-Gbps Eye Diagram (With TPD4E02B04)](image2)
9 Power Supply Recommendations

This device is a passive ESD device so there is no need to power it. Take care not to violate the recommended I/O specification (–3.6 V to 3.6 V) to ensure the device functions properly.

10 Layout

10.1 Layout Guidelines

- The optimum placement is as close to the connector as possible.
  - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
  - The PCB designer must minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TVS and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
  - Electric fields tend to build up on corners, increasing EMI coupling.

10.2 Layout Examples

Figure 24. USB Type-C Mid-Mount, Hybrid Connector with One-Sided ESD Layout

Legend

- Top Layer
- Bottom Layer
- Pin to GND
- VIA to VBUS Plane
- VIA to Other Layer
- VIA to GND Plane
Figure 25. HDMI2.0 Type-A Transmitter Port Layout
11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation see the following:

- Reading and Understanding an ESD Protection Datasheet, SLLA305
- ESD Layout Guide, SLVA680
- Picking ESD Diodes for Ultra High-Speed Data Lines, SLVA785
- TPD4E02B04EVM Users Guide, SLVUAH6

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on Alert me to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.4 Trademarks

E2E is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

11.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.
## PACKAGING INFORMATION

<table>
<thead>
<tr>
<th>Orderable Device</th>
<th>Status (1)</th>
<th>Package Type</th>
<th>Package Drawing</th>
<th>Pins</th>
<th>Package Qty</th>
<th>Eco Plan (2)</th>
<th>Lead finish/ Ball material</th>
<th>MSL Peak Temp (3)</th>
<th>Op Temp (°C)</th>
<th>Device Marking (4/5)</th>
<th>Samples</th>
</tr>
</thead>
<tbody>
<tr>
<td>TPD4E02B04DQAR</td>
<td>ACTIVE</td>
<td>USON</td>
<td>DQA</td>
<td>10</td>
<td>3000</td>
<td>RoHS &amp; Green</td>
<td>NIPDAU</td>
<td>Level-1-260C-UNLIM</td>
<td>-40 to 125</td>
<td>1SG 1SY</td>
<td></td>
</tr>
</tbody>
</table>

(1) The marketing status values are defined as follows:
- **ACTIVE**: Product device recommended for new designs.
- **LIFEBUY**: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
- **NRND**: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
- **PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.
- **OBSOLETE**: TI has discontinued the production of the device.

(2) **RoHS**: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as “Pb-Free”.

**RoHS Exempt**: TI defines “RoHS Exempt” to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green**: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) **MSL, Peak Temp.** - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TPD4E02B04:

- Automotive: TPD4E02B04-Q1

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
**TAPE AND REEL INFORMATION**

*All dimensions are nominal*

<table>
<thead>
<tr>
<th>Device</th>
<th>Package Type</th>
<th>Package Drawing</th>
<th>Pins</th>
<th>SPQ</th>
<th>Reel Diameter (mm)</th>
<th>Reel Width W1 (mm)</th>
<th>A0 (mm)</th>
<th>B0 (mm)</th>
<th>K0 (mm)</th>
<th>P1 (mm)</th>
<th>W (mm)</th>
<th>Pin1 Quadrant</th>
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<tr>
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<td>USON</td>
<td>DQA</td>
<td>10</td>
<td>3000</td>
<td>180.0</td>
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<td>1.23</td>
<td>2.7</td>
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**TAPE AND REEL BOX DIMENSIONS**

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<th>Length (mm)</th>
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<tbody>
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<td>DQA</td>
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<td>3000</td>
<td>189.0</td>
<td>185.0</td>
<td>36.0</td>
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*All dimensions are nominal*
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
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